

SCES386L-MARCH 2002-REVISED JULY 2009

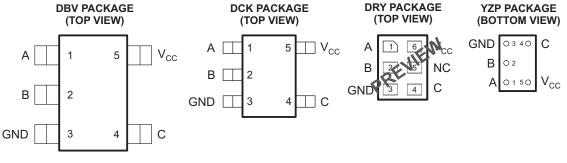
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### SINGLE BILATERAL ANALOG SWITCH

#### FEATURES

- Available in the Texas Instruments NanoFree™ Package
- Wide  $V_{CC}$  Range of 0.8 V to 2.7 V
- Sub-1-V Operable
- Low Power Consumption, 10-µA Max I<sub>CC</sub>
- **High On-Off Output Voltage Ratio**
- **High Degree of Linearity**
- High Speed Max 0.2 ns ( $V_{CC}$  = 1.8 V,  $C_{L} = 15 \text{ pF}$

- Low On-State Impedance Typically 9  $\Omega$  $(V_{CC} = 2.3 V)$
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- **ESD Protection Exceeds JESD 22** 
  - 2000-V Human-Body Model (A114-A)
  - 200-V Machine Model (A115-A) -
  - 1000-V Charged-Device Model (C101)



See mechanical drawings for dimensions. NC- No internal connection

### **DESCRIPTION/ORDERING INFORMATION**

This single analog switch is operational at 0.8-V to 2.7-V V<sub>CC</sub>, but is designed specifically for 1.65-V to 1.95-V V<sub>CC</sub> operation.

The SN74AUC1G66 can handle both analog and digital signals. The combined AC and DC signal has to be between V<sub>CC</sub> and GND for it to be transmitted in either direction.

NanoFree™ package technology is a major breakthrough in IC packaging concepts, using the die as the package.

Applications include signal gating, chopping, modulation or demodulation (modem), and signal multiplexing for analog-to-digital and digital-to-analog conversion systems.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet. NanoFree is a trademark of Texas Instruments.

### SN74AUC1G66

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#### **ORDERING INFORMATION**

T <sub>A</sub>	PACKAGE <sup>(1)(2)</sup>		ORDERABLE PART NUMBER	TOP-SIDE MARKING <sup>(3)</sup>
	NanoFree™ WCSP (DSBGA) – YZP (Pb-free)	Reel of 3000	SN74AUC1G66YZPR	U6_
-40°C to 85°C	SON – DRY	Reel of 5000	SN74AUC1G66DRYR	PREVIEW
	SOT (SOT-23) – DBV	Reel of 3000	SN74AUC1G66DBVR	U66_
	SOT (SC-70) – DCK	Reel of 3000	SN74AUC1G66DCKR	U6_

(1) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.

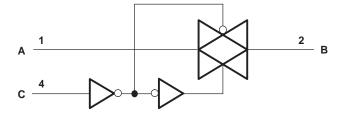
(2) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.

(3) DBV/DCK/DRY: The actual top-side marking has one additional character that designates the assembly/test site. YZP: The actual top-side marking has three preceding characters to denote year, month, and sequence code, and one following character to designate the assembly/test site.

CONTROL INPUT (C)	SWITCH
L	OFF
Н	ON

#### **FUNCTION TABLE**

#### LOGIC DIAGRAM (POSITIVE LOGIC)



#### Absolute Maximum Ratings<sup>(1)</sup>

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage range		-0.5	3.6	V
VI	Input voltage range <sup>(2)</sup>		-0.5	3.6	V
V <sub>I/O</sub>	Switch I/O voltage range <sup>(2)(3)</sup>		-0.5	V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	Control input clamp current	V <sub>1</sub> < 0		-50	mA
I <sub>IOK</sub>	I/O port diode current	$V_{I/O} < 0 \text{ or } V_{I/O} > V_{CC}$		±50	mA
IT	On-state switch current	$V_{I/O} = 0$ to $V_{CC}$		±50	mA
	Continuous current through V <sub>CC</sub> or GND			±100	mA
		DBV package		206	
0	Package thermal impedance <sup>(4)</sup>	DCK package		252	°C/W
$\theta_{JA}$	Package inermai impedance	DRY package		234	°C/W
		YZP package		123	
T <sub>stg</sub>	Storage temperature range		-65	150	°C

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltages are with respect to ground, unless otherwise specified.

(3) The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.

(4) The package thermal impedance is calculated in accordance with JESD 51-7.



#### **Recommended Operating Conditions**<sup>(1)</sup>

			MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage High-level input voltage Low-level input voltage I/O port voltage Control input voltage		0.8	2.7	V
		V <sub>CC</sub> = 0.8 V	V <sub>CC</sub>		
V <sub>IH</sub>	High-level input voltage	$V_{CC} = 1.1 \text{ V to } 1.95 \text{ V}$	0.65 × V <sub>CC</sub>		V
		$V_{CC}$ = 2.3 V to 2.7 V	1.7		
		V <sub>CC</sub> = 0.8 V		0	
V <sub>IL</sub>	Low-level input voltage	$V_{CC} = 1.1 \text{ V to } 1.95 \text{ V}$		$0.35 \times V_{CC}$	V
		$V_{CC}$ = 2.3 V to 2.7 V		0.7	
V <sub>I/O</sub>	I/O port voltage		0	V <sub>CC</sub>	V
VI	Control input voltage		0	3.6	V
Δt/Δv	Input transition rise or fall rate			20	ns/V
T <sub>A</sub>	Operating free-air temperature		-40	85	°C

 All unused inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

#### **Electrical Characteristics**

over recommended operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDIT	IONS	V <sub>cc</sub>	MIN TYP <sup>(1)</sup>	MAX	UNIT
	<b>2</b>	$V_{I} = V_{CC}$ or GND,	$I_{S} = 4 \text{ mA}$	1.65 V	10	20	-
r <sub>on</sub>	On-state switch resistance	V <sub>C</sub> = V <sub>IH</sub> (see Figure 1)	$I_{\rm S}$ = 8 mA	2.3 V	9	15	Ω
		$V_I = V_{CC}$ to GND,	$I_{\rm S} = 4 \text{ mA}$	1.65 V	32	80	
r <sub>on(p)</sub>	Peak on resistance	V <sub>C</sub> = V <sub>IH</sub> (see Figure 1)	$I_{S} = 8 \text{ mA}$	2.3 V	15	20	Ω
	<b>0</b> <i>11</i>	$V_{I} = V_{CC}$ and $V_{O} = GND$ ,	or			±1	
I <sub>S(off)</sub>	Off-state switch leakage current	$V_I = GND \text{ and } V_O = V_{CC},$ $V_C = V_{IL} \text{ (see Figure 2)}$		2.7 V		$\pm 0.1^{(1)}$	μA
	On state switch lookage switcht	$V_1 = V_{CC}$ or GND, $V_C = V$	′ <sub>IH</sub> , V <sub>O</sub> = Open	2.7 V		±1	۵
I <sub>S(on)</sub>	On-state switch leakage current	(see Figure 3)		2.7 V		±0.1 <sup>(1)</sup>	μA
I <sub>I</sub>	Control input current	$V_I = V_{CC}$ or GND		0 to 2.7 V		±5	μA
I <sub>CC</sub>	Supply current	$V_I = V_{CC}$ or GND,	$I_{O} = 0$	0.8 V to 2.7 V		10	μA
C <sub>ic</sub>	Control input capacitance			2.5 V	2		pF
C <sub>io(off)</sub>	Switch input/output capacitance			2.5 V	3.5		pF
C <sub>io(on)</sub>	Switch input/output capacitance			2.5 V	7		pF

(1) All typical values are at  $T_A = 25^{\circ}C$ .

#### **Switching Characteristics**

over recommended operating free-air temperature range,  $C_L = 15 \text{ pF}$  (unless otherwise noted) (see Figure 4)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V <sub>CC</sub> = 0.8 V	V <sub>CC</sub> = ± 0.		V <sub>CC</sub> = ± 0.	1.5 V 1 V		<sub>c</sub> = 1.8 0.15 V		V <sub>CC</sub> = ± 0.		UNIT
		(001F01)	TYP	MIN	MAX	MIN	MAX	MIN	TYP	MAX	MIN	MAX	
t <sub>pd</sub> <sup>(1)</sup>	A or B	B or A	0.9		0.3		0.2			0.2		0.1	ns
t <sub>en</sub>	С	A or B	4.1	0.5	2.6	0.5	1.7	0.5	0.8	1.1	0.5	1	ns
t <sub>dis</sub>	С	A or B	5	0.7	3.6	0.5	2.6	0.5	1.7	2.9	0.5	2.2	ns

(1) The propagation delay is the calculated RC time constant of the typical on-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).

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#### **Switching Characteristics**

over recommended operating free-air temperature range,  $C_L = 30 \text{ pF}$  (unless otherwise noted) (see Figure 4)

PARAMETER	FROM (INPUT)	TO (OUTPUT)		<sub>c</sub> = 1.8 0.15 V		V <sub>CC</sub> = ± 0.	2.5 V 2 V	UNIT
	(INFUT)	(001F01)	MIN	TYP	MAX	MIN	MAX	
t <sub>pd</sub> <sup>(1)</sup>	A or B	B or A			0.3		0.3	ns
t <sub>en</sub>	С	A or B	0.5	1.4	2.3	0.8	1.4	ns
t <sub>dis</sub>	С	A or B	0.5	1.7	2.9	0.5	1.5	ns

(1) The propagation delay is the calculated RC time constant of the typical on-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).



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#### **Analog Switch Characteristics**

 $T_A = 25^{\circ}C$ 

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	V <sub>cc</sub>	TYP	UNIT
				0.8 V	60	
			$C_{L} = 50 \text{ pF}, R_{L} = 600 \Omega,$	1.1 V	60	
			f <sub>in</sub> = sine wave	1.4 V	80	
			(see Figure 5)	1.65 V	120	
Frequency response <sup>(1)</sup>	A or B	B or A		2.3 V	170	MHz
(switch ON)	AOD	BUIA		0.8 V	>500	
			$C_{L} = 5 \text{ pF}, R_{L} = 50 \Omega,$	1.1 V	>500	
			f <sub>in</sub> = sine wave	1.4 V	>500	
			(see Figure 5)	1.65 V	>500	
				2.3 V	>500	
				0.8 V	9	
			$C_{L} = 50 \text{ pF}, R_{L} = 600 \Omega,$	1.1 V	14	
Crosstalk control input to signal output)	С	A or B	f <sub>in</sub> = 1 MHz (square wave)	1.4 V	15	mV
			(see Figure 6)	1.65 V	16	
				2.3 V	20	
				0.8 V	-60	dB
			$C_{L} = 50 \text{ pF}, R_{L} = 600 \Omega,$	1.1 V	-60	
			f <sub>in</sub> = 1 MHz (sine wave)	1.4 V	-60	
			(see Figure 7)	1.65 V	-60	
eedthrough attenuation <sup>(2)</sup>	A or B	B or A		2.3 V	-60	
switch OFF)	AUB	BUIA		0.8 V	-55	
			$C_{L} = 5 \text{ pF}, R_{L} = 50 \Omega,$	1.1 V	-55	
			f <sub>in</sub> = 1 MHz (sine wave)	1.4 V	-55	
			(see Figure 7)	1.65 V	-55	
				2.3 V	-55	
				0.8 V	7.5	
			C <sub>L</sub> = 50 pF, R <sub>L</sub> = 10 kΩ,	1.1 V	0.16	
	A or B	B or A	f <sub>in</sub> = 1 kHz (sine wave)	1.4 V	0.04	
			(see Figure 8)	1.65 V	0.03	
Sine-wave distortion				2.3 V	0.02	%
				0.8 V	4.2	70
			C <sub>L</sub> = 50 pF, R <sub>L</sub> = 10 kΩ,	1.1 V	0.2	
	A or B	B or A	f <sub>in</sub> = 10 kHz (sine wave)	1.4 V	0.03	3
		DUA	(see Figure 8)	1.65 V	0.02	
				2.3 V	0.02	

 $\begin{array}{ll} \mbox{(1)} & \mbox{Adjust} \ f_{in} \ \mbox{voltage to obtain 0 dBm at output. Increase} \ f_{in} \ \mbox{frequency until dB meter reads} \ -3 \ \mbox{dB.} \\ \mbox{(2)} & \mbox{Adjust} \ f_{in} \ \mbox{voltage to obtain 0 dBm at input.} \end{array}$ 

#### **Operating Characteristics**

 $T_A = 25^{\circ}C$ 

	PARAMETER	TEST     V <sub>CC</sub> = 0.8 V       CONDITIONS     TYP		V <sub>CC</sub> = 1.2 V TYP	V <sub>CC</sub> = 1.5 V TYP	V <sub>CC</sub> = 1.8 V TYP	V <sub>CC</sub> = 2.5 V TYP	UNIT
$C_{\text{pd}}$	Power dissipation capacitance	f = 10 MHz	3	3	3	3	3	pF



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PARAMETER MEASUREMENT INFORMATION

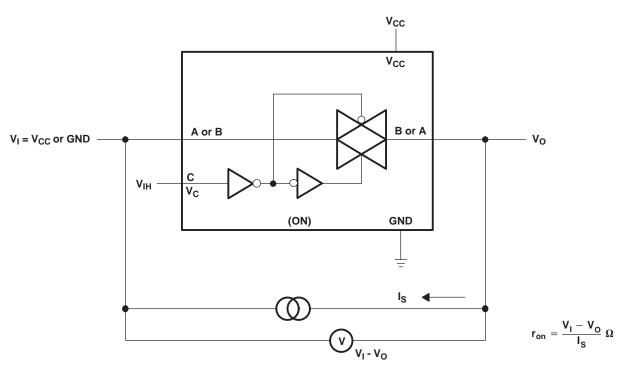


Figure 1. On-State Resistance Test Circuit

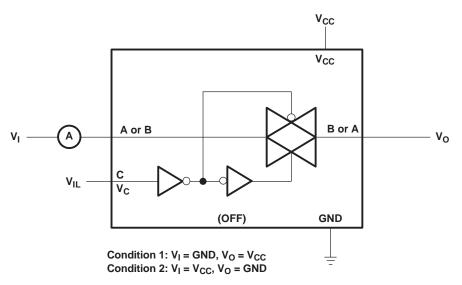


Figure 2. Off-State Switch Leakage-Current Test Circuit



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PARAMETER MEASUREMENT INFORMATION (Continued)

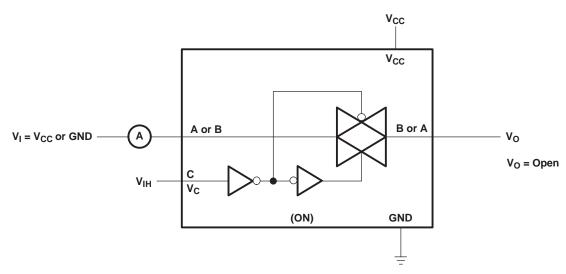
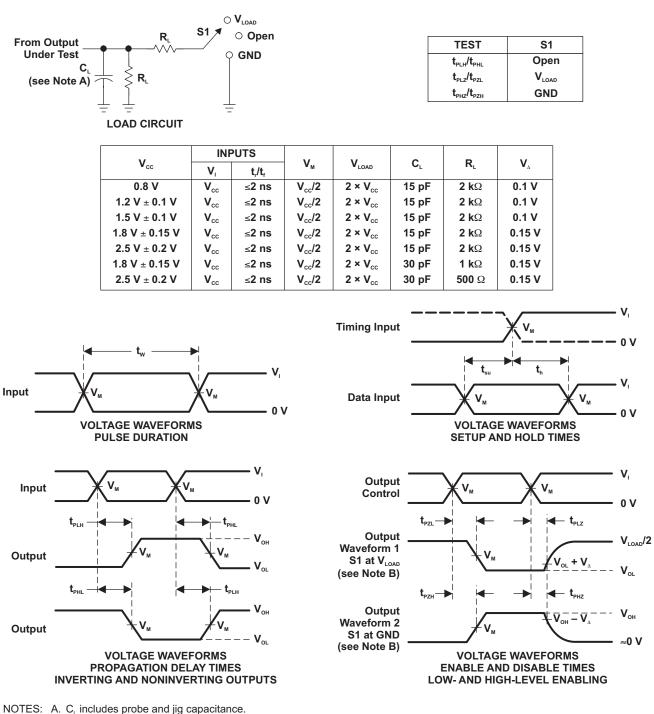


Figure 3. On-State Leakage-Current Test Circuit

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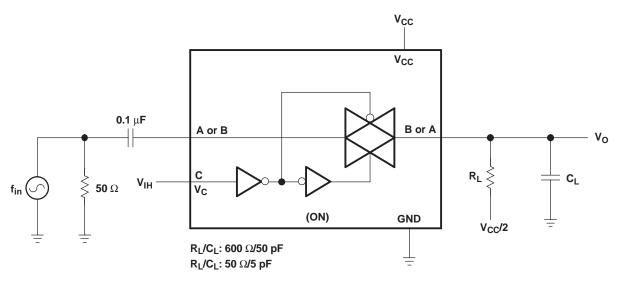


**PARAMETER MEASUREMENT INFORMATION (Continued)** 

- - B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control. C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz, Z<sub>o</sub> = 50  $\Omega$ , Slew rate  $\geq$  1 V/ns.
  - D. The outputs are measured one at a time, with one transition per measurement.
  - E.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis}$ .
  - F.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .
  - G.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{od}$ .

#### Figure 4. Load Circuit and Voltage Waveforms





#### PARAMETER MEASUREMENT INFORMATION (Continued)



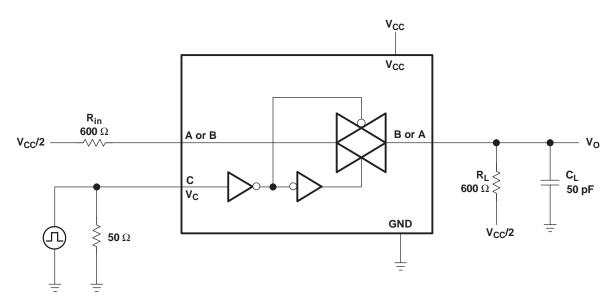


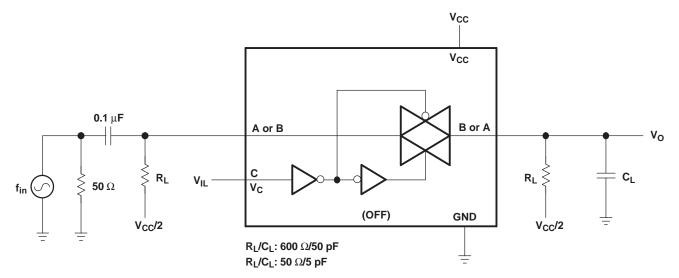
Figure 6. Crosstalk (Control Input – Switch Output)

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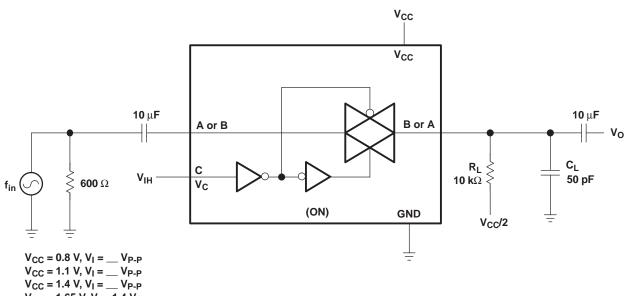
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 $V_{CC} = 1.4$  V,  $V_I = \__V_{P-P}$   $V_{CC} = 1.65$  V,  $V_I = 1.4$  V<sub>P-P</sub>  $V_{CC} = 2.3$  V,  $V_I = 2.5$  V<sub>P-P</sub>





#### PACKAGING INFORMATION

Orderable Device		Package Type	Package Drawing	Pins	-		Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
SN74AUC1G66DBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-40 to 85	(U66F, U66R)	Samples
SN74AUC1G66DCKR	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(U65, U6F, U6R)	Samples
SN74AUC1G66YZPR	ACTIVE	DSBGA	YZP	5	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	U6N	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

<sup>(6)</sup> Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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STRUMENTS

#### TAPE AND REEL INFORMATION





#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74AUC1G66DBVR	SOT-23	DBV	5	3000	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
SN74AUC1G66DBVR	SOT-23	DBV	5	3000	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
SN74AUC1G66DCKR	SC70	DCK	5	3000	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74AUC1G66DCKR	SC70	DCK	5	3000	180.0	8.4	2.47	2.3	1.25	4.0	8.0	Q3
SN74AUC1G66DCKR	SC70	DCK	5	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74AUC1G66YZPR	DSBGA	YZP	5	3000	178.0	9.2	1.02	1.52	0.63	4.0	8.0	Q1



## PACKAGE MATERIALS INFORMATION

17-Mar-2024



Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74AUC1G66DBVR	SOT-23	DBV	5	3000	202.0	201.0	28.0
SN74AUC1G66DBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
SN74AUC1G66DCKR	SC70	DCK	5	3000	180.0	180.0	18.0
SN74AUC1G66DCKR	SC70	DCK	5	3000	202.0	201.0	28.0
SN74AUC1G66DCKR	SC70	DCK	5	3000	180.0	180.0	18.0
SN74AUC1G66YZPR	DSBGA	YZP	5	3000	220.0	220.0	35.0

# YZP0005



## **PACKAGE OUTLINE**

### DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.



# YZP0005

# **EXAMPLE BOARD LAYOUT**

### DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).



# YZP0005

# **EXAMPLE STENCIL DESIGN**

### DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.



# **DBV0005A**



## **PACKAGE OUTLINE**

### SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
  This drawing is subject to change without notice.
  Reference JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
- 5. Support pin may differ or may not be present.



## DBV0005A

# **EXAMPLE BOARD LAYOUT**

### SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



## DBV0005A

## **EXAMPLE STENCIL DESIGN**

### SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

9. Board assembly site may have different recommendations for stencil design.



# **DCK0005A**



## **PACKAGE OUTLINE**

### SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
  This drawing is subject to change without notice.
  Reference JEDEC MO-203.

- 4. Support pin may differ or may not be present.5. Lead width does not comply with JEDEC.



## **DCK0005A**

# **EXAMPLE BOARD LAYOUT**

### SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



## DCK0005A

# **EXAMPLE STENCIL DESIGN**

### SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

9. Board assembly site may have different recommendations for stencil design.



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